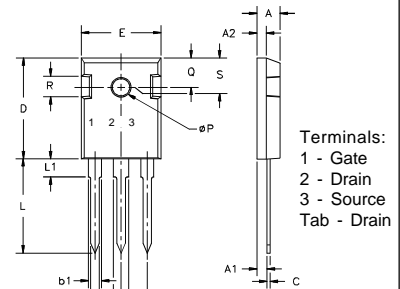


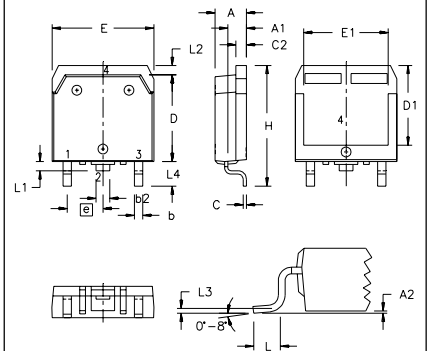
| Symbol | Test Conditions | Characteristic Values ($T_j = 25^\circ\text{C}$, unless otherwise specified) | | |
|--------------|--|---|------|------|
| | | min. | typ. | max. |
| g_{fs} | $V_{DS} = 15\text{ V}; I_D = 0.5 \cdot I_{D25}$, pulse test | 4 | 10 | S |
| C_{iss} | $V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$ | | 2900 | pF |
| C_{oss} | | | 315 | pF |
| C_{rss} | | | 50 | pF |
| $t_{d(on)}$ | $V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ $R_G = 2\ \Omega$ (External), | | 20 | ns |
| t_r | | | 23 | ns |
| $t_{d(off)}$ | | | 40 | ns |
| t_f | | | 15 | ns |
| $Q_{g(on)}$ | $V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ | | 90 | nC |
| Q_{gs} | | | 30 | nC |
| Q_{gd} | | | 40 | nC |
| R_{thJC} | | | 0.42 | K/W |
| R_{thCK} | (TO-247) | | 0.25 | K/W |

| Source-Drain Diode | | Characteristic Values ($T_j = 25^\circ\text{C}$, unless otherwise specified) | | |
|--------------------|---|---|------|---------------|
| Symbol | Test Conditions | min. | typ. | max. |
| I_S | $V_{GS} = 0\text{ V}$ | | | 12 A |
| I_{SM} | Repetitive; pulse width limited by T_{JM} | | | 48 A |
| V_{SD} | $I_F = I_S, V_{GS} = 0\text{ V}$, Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$ | | | 1.5 V |
| t_{rr} | $I_F = I_S, -di/dt = 100\text{ A}/\mu\text{s}, V_R = 100\text{ V}$ | | 200 | ns |
| Q_{RM} | | | 0.6 | μC |
| I_{RM} | | | 7 | A |

TO-247 AD (IXFH) Outline


Terminals:
 1 - Gate
 2 - Drain
 3 - Source
 Tab - Drain

| Dim. | Millimeter | | Inches | |
|----------------|------------|-------|--------|-------|
| | Min. | Max. | Min. | Max. |
| A | 4.7 | 5.3 | .185 | .209 |
| A ₁ | 2.2 | 2.54 | .087 | .102 |
| A ₂ | 2.2 | 2.6 | .087 | .102 |
| b | 1.0 | 1.4 | .040 | .055 |
| b ₁ | 1.65 | 2.13 | .065 | .084 |
| b ₂ | 2.87 | 3.12 | .113 | .123 |
| C | .4 | .8 | .016 | .031 |
| D | 20.80 | 21.46 | .819 | .845 |
| E | 15.75 | 16.26 | .610 | .640 |
| e | 5.20 | 5.72 | 0.205 | 0.225 |
| L | 19.81 | 20.32 | .780 | .800 |
| L1 | | 4.50 | | .177 |
| ØP | 3.55 | 3.65 | .140 | .144 |
| Q | 5.89 | 6.40 | 0.232 | 0.252 |
| R | 4.32 | 5.49 | .170 | .216 |
| S | 6.15 | BSC | .242 | BSC |

TO-268 Outline


| SYM | INCHES | | MILLIMETERS | |
|-----|--------|------|-------------|-------|
| | MIN | MAX | MIN | MAX |
| A | .193 | .201 | 4.90 | 5.10 |
| A1 | .106 | .114 | 2.70 | 2.90 |
| A2 | .001 | .010 | 0.02 | 0.25 |
| b | .045 | .057 | 1.15 | 1.45 |
| b2 | .075 | .083 | 1.90 | 2.10 |
| C | .016 | .026 | 0.40 | 0.65 |
| C2 | .057 | .063 | 1.45 | 1.60 |
| D | 54.3 | 55.1 | 13.80 | 14.00 |
| D1 | 48.8 | 50.0 | 12.40 | 12.70 |
| E | 62.4 | 63.2 | 15.85 | 16.05 |
| E1 | 52.4 | 53.5 | 13.30 | 13.60 |
| e | .215 | BSC | 5.45 | BSC |
| H | .736 | .752 | 18.70 | 19.10 |
| L | .094 | .106 | 2.40 | 2.70 |
| L1 | .047 | .055 | 1.20 | 1.40 |
| L2 | .039 | .045 | 1.00 | 1.15 |
| L3 | .010 | BSC | 0.25 | BSC |
| L4 | .150 | .161 | 3.80 | 4.10 |

IXYS reserves the right to change limits, test conditions, and dimensions.

| | | | | | | | |
|--|-----------|-----------|-----------|-----------|-----------|-----------|-------------|
| IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: | 4,835,592 | 4,881,106 | 5,017,508 | 5,049,961 | 5,187,117 | 5,486,715 | 6,306,728B1 |
| | 4,850,072 | 4,931,844 | 5,034,796 | 5,063,307 | 5,237,481 | 5,381,025 | |

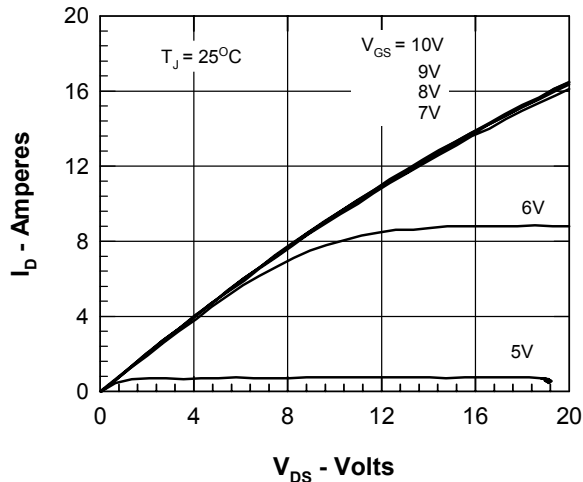


Figure 1. Output Characteristics at 25°C

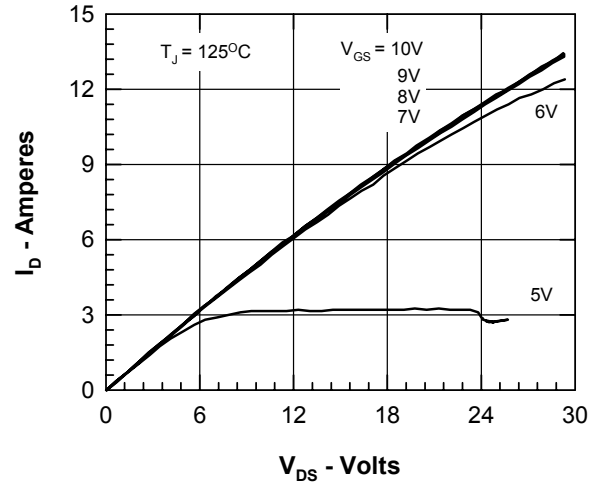


Figure 2. Output Characteristics at 125°C

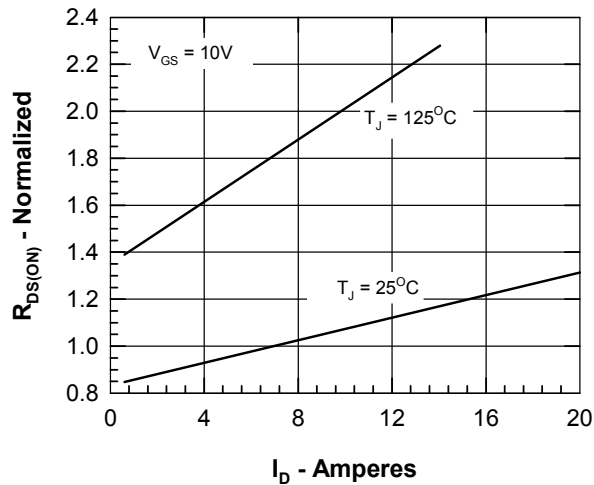


Figure 3. $R_{DS(on)}$ normalized to value at $I_D = 12A$

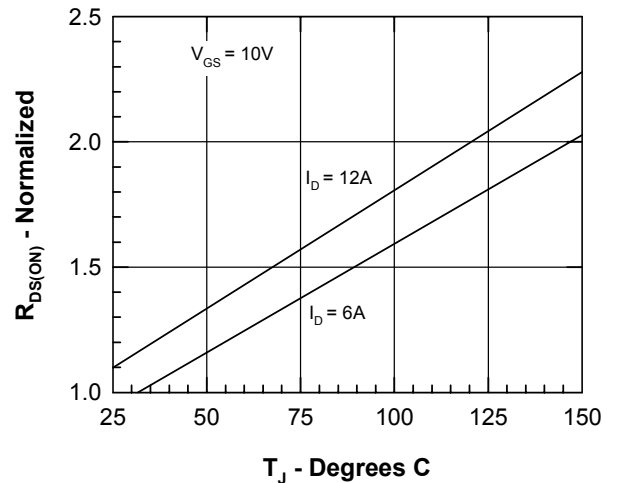


Figure 4. $R_{DS(on)}$ normalized to value at $I_D = 12A$

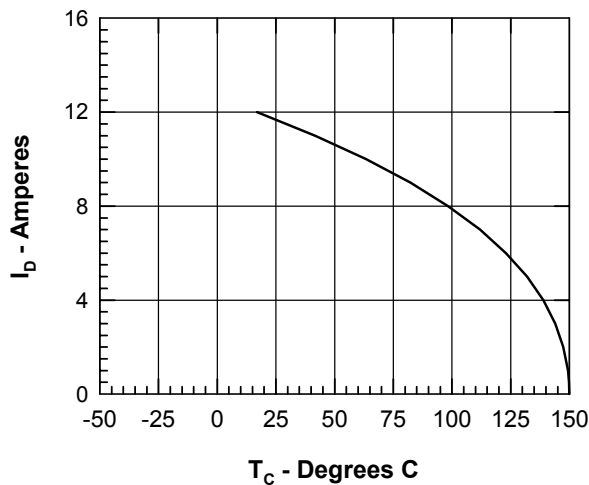


Figure 5. Drain Current vs. Case Temperature

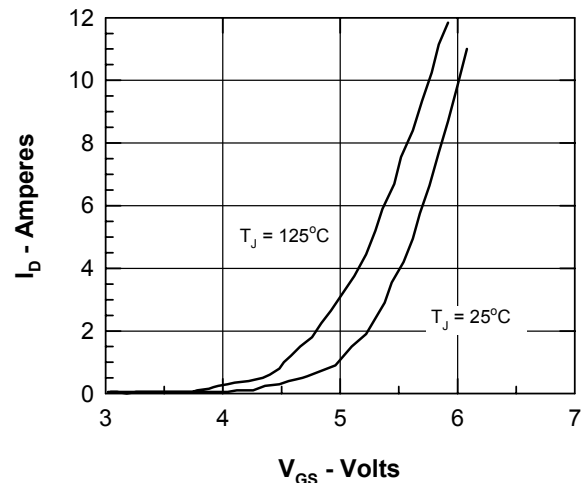


Figure 6. Admittance Curves

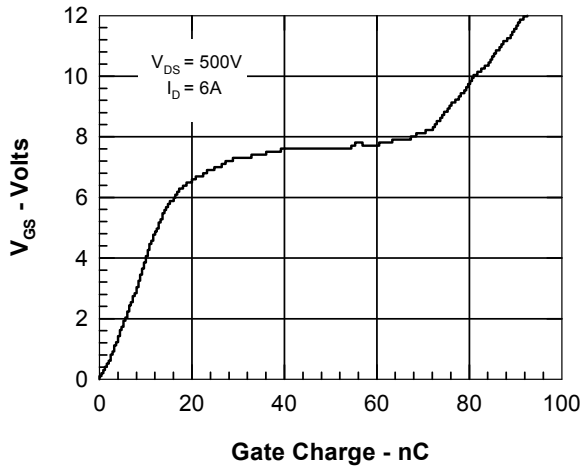


Figure 7. Gate Charge

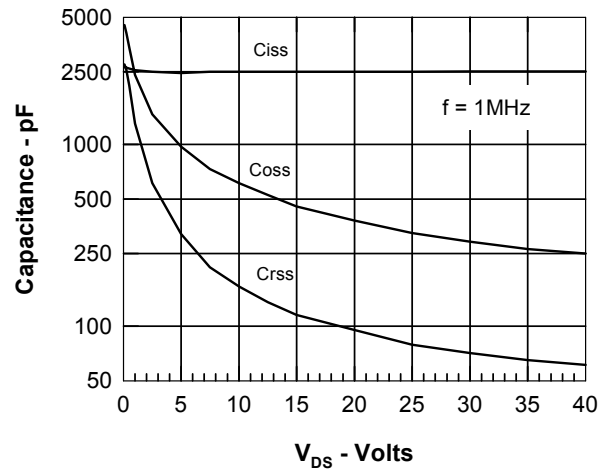


Figure 8. Capacitance Curves

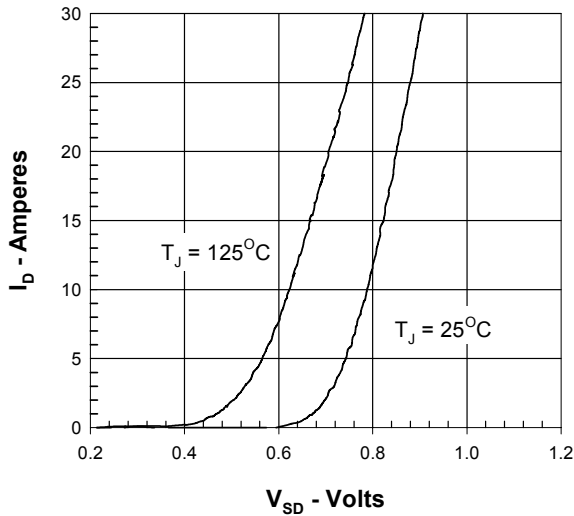


Figure 9. Source Current vs. Source to Drain Voltage

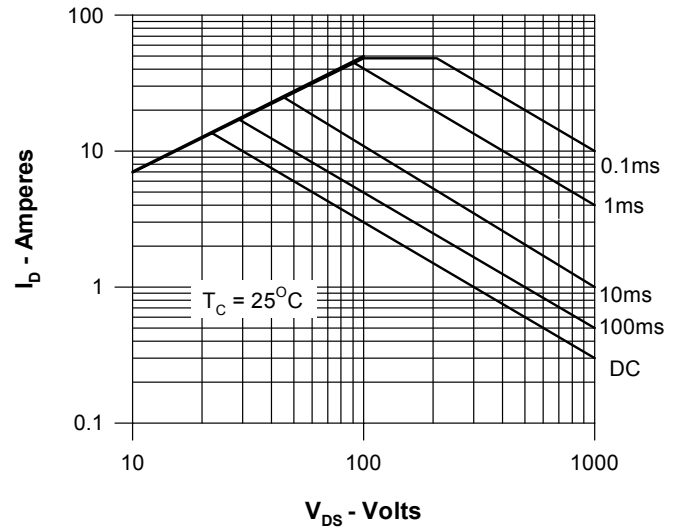


Figure 10. Forward Bias Safe Operating Area

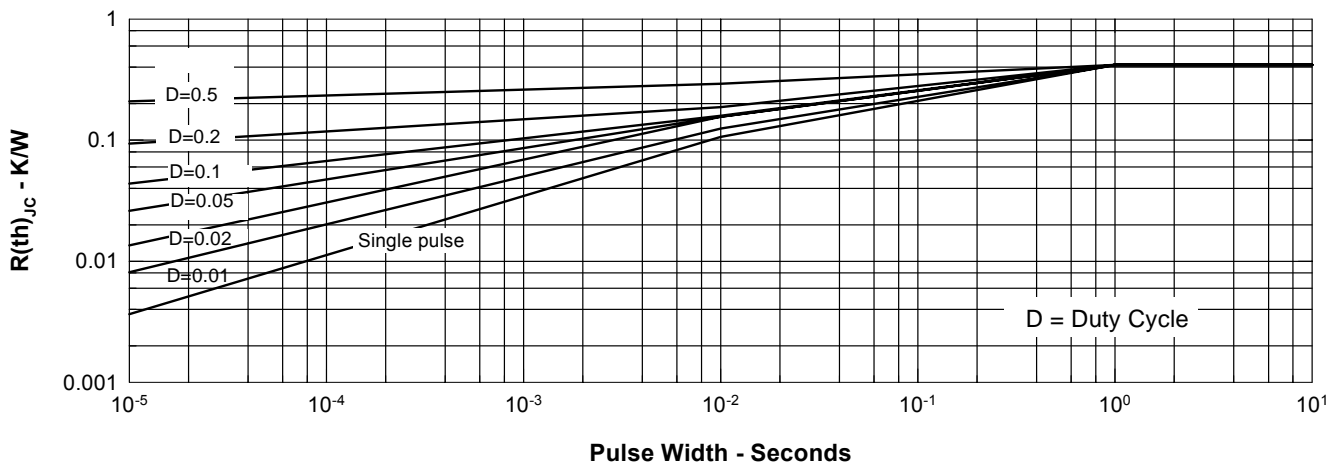


Figure 11. Transient Thermal Resistance

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| | | | | | | |
|-----------|-----------|-----------|-----------|-----------|-----------|-------------|
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| 4,850,072 | 4,931,844 | 5,034,796 | 5,063,307 | 5,237,481 | 5,381,025 | |



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